

L Number	Hits	Search Text	DB	Time stamp
36	8	spontaneous near emission near absorbing	USPAT	2003/07/11 11:19
37	4	In"x"GaN1-x"N	USPAT	2003/07/11 11:32
38	0	In"x"GaN1-x"N and active and clad\$5 and contact and substrate	USPAT	2003/07/11 11:33
-	149	(nitride near semiconductor) and (buffer near layer) and (active near layer) and (clad\$5 near layer) and indium	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/11 11:12
-	131	(nitride near semiconductor) and (buffer near layer) and (active near layer) and (clad\$5 near layer) and indium and substrate and electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/19 14:50
-	20	(nitride near semiconductor) and ((buffer near layer) with indium) and (active near layer) and (clad\$5 near layer) and substrate and electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/19 17:22
-	28	(nitride near semiconductor) and (buffer near layer) and (active near layer) and (clad\$5 near layer) and indium and substrate and electrode and absorb\$6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/19 14:52
-	21	((nitride near semiconductor) and (buffer near layer) and (active near layer) and (clad\$5 near layer) and indium and substrate and electrode and absorb\$6) not ((nitride near semiconductor) and ((buffer near layer) with indium) and (active near layer) and (clad\$5 near layer) and substrate and electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/19 14:52
-	6	(laser near chip) and (photoelectric or (photo adj electric)) and block\$6 and buffer and substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/19 17:42
-	160	(laser near semiconductor) and (photoelectric or (photo adj electric)) and block\$6 and buffer and substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/11 11:18
-	14	(laser near semiconductor) and (photoelectric or (photo adj electric)) and block\$6 and buffer and substrate and (laser near3 chip)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/19 17:46
-	171	(laser near semiconductor) and (photoelectric or (photo adj electric) or (photodetector) (photodiode) or (photo adj detector) or (photo adj diode)) and block\$6 and buffer and substrate and (laser near3 chip)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/20 07:00
-	72	(semiconductor near laser near3 chip) and (photoelectric or (photo adj electric) or (photodetector) (photodiode) or (photo adj detector) or (photo adj diode)) and block\$6 and buffer and substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/20 07:03

-	40	(semiconductor near laser near3 chip) and (photoelectric or (photo adj electric) or (photodetector) or (photodiode) or (photo adj detector) or (photo adj diode)) and block\$6 and buffer and substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/20 10:59
-	23	((semiconductor near laser near3 chip) and (photoelectric or (photo adj electric) or (photodetector) or (photodiode) or (photo adj detector) or (photo adj diode)) and block\$6 and buffer and substrate) and 372/\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/20 07:29
-	5	(semiconductor near laser near3 chip) and ((photoelectric or (photo adj electric) or (photodetector) or (photodiode) or (photo adj detector) or (photo adj diode)) same block\$6) and buffer and substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/11 11:28
-	0	(semiconductor near laser near3 chip) and ((photoelectric or (photo adj electric) or (photodetector) or (photodiode) or (photo adj detector) or (photo adj diode)) same (block\$6 near layer)) and buffer and substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/20 11:01
-	26	(semiconductor near laser near3 chip) and (photoelectric or (photo adj electric) or (photodetector) or (photodiode) or (photo adj detector) or (photo adj diode)) and (block\$6 near layer) and buffer and substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/20 11:02
-	36	(semiconductor near laser) and (active with (In near3 Ga near3 N))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/20 09:41